

Albert Chin

List of Publications by Year in descending order

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times ranked

4642
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#	ARTICLE	IF	CITATIONS
1	Remarkably High-Performance Nanosheet GeSn Thin-Film Transistor. <i>Nanomaterials</i> , 2022, 12, 261.	4.1	3
2	Oxygen vacancies in zirconium oxide as the blue luminescence centres and traps responsible for charge transport: Part II—Films. <i>Materialia</i> , 2021, 15, 100980.	2.7	8
3	Exceedingly High Performance Top-Gate P-Type SnO Thin Film Transistor with a Nanometer Scale Channel Layer. <i>Nanomaterials</i> , 2021, 11, 92.	4.1	18
4	Charge transport mechanism in the forming-free memristor based on silicon nitride. <i>Scientific Reports</i> , 2021, 11, 2417.	3.3	21
5	43.2: Invited Paper: High Mobility Oxide Complementary TFTs for System-on-Chip Display and Three-Dimensional Brain-Mimicking IC. <i>Digest of Technical Papers SID International Symposium</i> , 2021, 52, 292-294.	0.3	1
6	High-Power Switch Using LC Resonator and Asymmetric MOS Transistor for 5G Applications. <i>IEEE Microwave and Wireless Components Letters</i> , 2021, 31, 304-307.	3.2	1
7	Improved Device Distribution in High-Performance SiNx Resistive Random Access Memory via Arsenic Ion Implantation. <i>Nanomaterials</i> , 2021, 11, 1401.	4.1	16
8	Effects of Microwave and Furnace Annealing for P-Type SnO Thin Film Material in Oxygen Ambient. <i>Journal of Nanoscience and Nanotechnology</i> , 2021, 21, 4763-4767.	0.9	0
9	A Wide Tuning-Range Triple-Mode CMOS VCO Using Switched-Tunable Inductor. <i>IEEE Microwave and Wireless Components Letters</i> , 2021, 31, 1063-1066.	3.2	5
10	A Switched Tunable Inductor Based on Magnetic Flux Linkage Modification. <i>IEEE Electron Device Letters</i> , 2021, 42, 6-9.	3.9	2
11	Silicon Nanocrystals and Amorphous Nanoclusters in SiO _x and SiNx: Atomic, Electronic Structure, and Memristor Effects. , 2020, , .		1
12	Realization of an IGBT Gate Driver With Dualphase Turn-On/Off Gate Control. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 1089-1095.	2.1	3
13	High-Performance Top-Gate Thin-Film Transistor with an Ultra-Thin Channel Layer. <i>Nanomaterials</i> , 2020, 10, 2145.	4.1	13
14	High Performance All Nonmetal SiNx Resistive Random Access Memory with Strong Process Dependence. <i>Scientific Reports</i> , 2020, 10, 2807.	3.3	24
15	Reliability of Atmosphere Pressure-Plasma Enhanced Chemical Vapor Deposition Deposited Indium Gallium Zinc Oxide Resistive Random Access Memory Device with Microwave Annealing. <i>Journal of Nanoscience and Nanotechnology</i> , 2020, 20, 4057-4060.	0.9	1
16	Electronic structure and charge transport mechanism in a forming-free SiO _x -based memristor. <i>Nanotechnology</i> , 2020, 31, 505704.	2.6	12
17	Study of Atmospheric-Pressure Plasma Enhanced Chemical Vapor Deposition Fabricated Indium Gallium Zinc Oxide Thin Film Transistors with In-Situ Hydrogen Plasma Treatment. <i>Journal of Nanoscience and Nanotechnology</i> , 2020, 20, 4110-4113.	0.9	2
18	Investigation of Microwave Annealing on Resistive Random Access Memory Device with Atmospheric Pressure Plasma Enhanced Chemical Vapor Deposition Deposited IGZO Layer. <i>Journal of Nanoscience and Nanotechnology</i> , 2020, 20, 4244-4247.	0.9	2

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19	Electrical Characteristics of Magnesium Doped a-IGZO RRAM: Chemical Vapor Deposition using Enhanced Atmospheric Pressure-Plasma. , 2020, , .		1
20	Technologies Toward Three-Dimensional Brain-Mimicking IC Architecture. , 2019, , .		1
21	Low-Temperature Processed Tin Oxide Transistor With Ultraviolet Irradiation. IEEE Electron Device Letters, 2019, 40, 909-912.	3.9	13
22	Nanoscale potential fluctuations and electron percolation in silicon oxide (SiO _x , x = 1.4, 1.6). Materials Research Express, 2019, 6, 116409.	1.6	1
23	Charge transport mechanism of high-resistive state in RRAM based on SiO _x . Applied Physics Letters, 2019, 114, .	3.3	18
24	Memristor effect in GeO[SiO ₂] and GeO[SiO] solid alloys films. Applied Physics Letters, 2019, 114, .	3.3	26
25	All Nonmetal Resistive Random Access Memory. Scientific Reports, 2019, 9, 6144.	3.3	24
26	Mechanism of stress induced leakage current in Si ₃ N ₄ . Materials Research Express, 2019, 6, 076401.	1.6	1
27	Atomic and Electronic Structures of a-SiN _x :H. Journal of Experimental and Theoretical Physics, 2019, 129, 924-934.	0.9	11
28	Forming-Free SiGeO _x /TiO _y Resistive Random Access Memories Featuring Large Current Distribution Windows. Journal of Nanoscience and Nanotechnology, 2019, 19, 7916-7919.	0.9	4
29	Charge transport mechanism in SiN _x -based memristor. Applied Physics Letters, 2019, 115, 253502.	3.3	21
30	An Offset Readout Current Sensing Scheme for One-Resistor RRAM-Based Cross-Point Array. IEEE Electron Device Letters, 2019, 40, 208-211.	3.9	19
31	Multiphonon trap ionization transport in nonstoichiometric SiN _x . Materials Research Express, 2019, 6, 036304.	1.6	3
32	High Mobility Metal-Oxide Devices for Display SoP and 3D Brain-Mimicking IC. Proceedings of the International Display Workshops, 2019, , 455.	0.1	4
33	Remarkably High Hole Mobility Metal-Oxide Thin-Film Transistors. Scientific Reports, 2018, 8, 889.	3.3	51
34	Local Oscillations of Silicon—Silicon Bonds in Silicon Nitride. Technical Physics Letters, 2018, 44, 424-427.	0.7	8
35	Short-Range Order and Charge Transport in SiO _x : Experiment and Numerical Simulation. Technical Physics Letters, 2018, 44, 541-544.	0.7	1
36	Tuning the Morphology of Isoindigo Donor—Acceptor Polymer Film for High Sensitivity Ammonia Sensor. Advanced Functional Materials, 2018, 28, 1803145.	14.9	47

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37	The Nature of Defects Responsible for Transport in a Hafnia-Based Resistive Random Access Memory Element. , 2017, , 493-504.		1
38	A Novel Read Scheme for Large Size One-Resistor Resistive Random Access Memory Array. Scientific Reports, 2017, 7, 42375.	3.3	41
39	Remarkably High Mobility Thin-Film Transistor on Flexible Substrate by Novel Passivation Material. Scientific Reports, 2017, 7, 1147.	3.3	34
40	PBTI Investigation of MoS ₂ -n-MOSFET With Al ₂ O ₃ Gate Dielectric. IEEE Electron Device Letters, 2017, 38, 677-680.	3.9	10
41	Impact of current distribution on RRAM array with high and low μ_{on}/μ_{off} devices. , 2017, , .		4
42	Optical Properties of TiO ₂ Films Deposited by Reactive Electron Beam Sputtering. Journal of Electronic Materials, 2017, 46, 6089-6095.	2.2	35
43	Charge transport in thin hafnium and zirconium oxide films. Optoelectronics, Instrumentation and Data Processing, 2017, 53, 184-189.	0.6	18
44	Oxygen Vacancy in Hafnia as a Blue Luminescence Center and a Trap of Charge Carriers. Journal of Physical Chemistry C, 2016, 120, 19980-19986.	3.1	47
45	High mobility SnO ₂ TFT for display and future IC. , 2016, , .		0
46	New Material Transistor with Record-High Field-Effect Mobility among Wide-Band-Gap Semiconductors. ACS Applied Materials & Interfaces, 2016, 8, 19187-19191.	8.0	23
47	High Performance Metal-Gate/High- κ GaN MOSFET With Good Reliability for Both Logic and Power Applications. IEEE Journal of the Electron Devices Society, 2016, 4, 246-252.	2.1	6
48	Foreword Special Issue on Advanced Technology for Ultra-Low Power Electronic Devices. IEEE Journal of the Electron Devices Society, 2016, 4, 203-204.	2.1	0
49	Remarkably high mobility ultra-thin-film metal-oxide transistor with strongly overlapped orbitals. Scientific Reports, 2016, 6, 19023.	3.3	44
50	Trapping and detrapping of oxide border traps in Al ₂ O ₃ gate dielectric in MoS ₂ n-MOSFETs under PBTI stress. , 2016, , .		0
51	Ferroelectric, small bandgap and wide bandgap materials for ultra-low power green electronic devices. , 2016, , .		1
52	Investigation of Traps at MoS ₂ /Al ₂ O ₃ Interface in nMOSFETs by Low-Frequency Noise. IEEE Electron Device Letters, 2016, 37, 516-518.	3.9	9
53	Extremely high mobility ultra-thin metal-oxide with ns ² np ² configuration. , 2015, , .		10
54	Charge transport in amorphous Hf _{0.5} Zr _{0.5} O ₂ . Applied Physics Letters, 2015, 106, .	3.3	29

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55	Nanoscale potential fluctuation in non-stoichiometric HfO _x and low resistive transport in RRAM. <i>Microelectronic Engineering</i> , 2015, 147, 165-167.	2.4	20
56	Ultra-low power green electronic devices. , 2015, , .		0
57	Smooth Muscle Cell Genome Browser: Enabling the Identification of Novel Serum Response Factor Target Genes. <i>PLoS ONE</i> , 2015, 10, e0133751.	2.5	48
58	Percolation conductivity in hafnium sub-oxides. <i>Applied Physics Letters</i> , 2014, 105, 262903.	3.3	15
59	Performance comparison of titanium-oxide resistive switching memories using GeO _x and AlO _x capping layers for flexible application. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 061502.	1.5	1
60	High-gain DR circular patch on-chip antenna based on standard CMOS technology for millimeter-wave applications. , 2014, , .		2
61	Origin of traps and charge transport mechanism in hafnia. <i>Applied Physics Letters</i> , 2014, 105, 222901.	3.3	38
62	Low-Leakage-Current DRAM-Like Memory Using a One-Transistor Ferroelectric MOSFET With a Hf-Based Gate Dielectric. <i>IEEE Electron Device Letters</i> , 2014, 35, 138-140.	3.9	110
63	Charge carrier transport mechanism in high- ϵ dielectrics and their based resistive memory cells. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2014, 50, 310-314.	0.6	3
64	High performance n ⁺ /p junction technology for high mobility Ge nMOSFET. , 2014, , .		0
65	Low-Voltage Steep Turn-On pMOSFET Using Ferroelectric High- κ Gate Dielectric. <i>IEEE Electron Device Letters</i> , 2014, 35, 274-276.	3.9	112
66	Nano-crystallized titanium oxide resistive memory with uniform switching and long endurance. <i>Applied Physics A: Materials Science and Processing</i> , 2013, 111, 203-207.	2.3	8
67	Evaluation of Temperature Stability of Trilayer Resistive Memories Using Work-Function Tuning. <i>Applied Physics Express</i> , 2013, 6, 041203.	2.4	1
68	$\text{Ni/GeO}_x/\text{TiO}_y/\text{TaN}$ RRAM on Flexible Substrate With Excellent Resistance Distribution. <i>IEEE Electron Device Letters</i> , 2013, 34, 505-507.	3.9	45
69	A low operating voltage IGZO TFT using LaLuO ₃ gate dielectric. , 2013, , .		0
70	GeO ₂ /PZT resistive random access memory devices with Ni electrode. , 2013, , .		0
71	Low power green electronic devices. , 2013, , .		0
72	Metal-Gate/High- κ /Ge nMOS at Small CET With Higher Mobility Than SiO_2/Si at Wide Range Carrier Densities. <i>IEEE Electron Device Letters</i> , 2013, 34, 163-165.	3.9	10

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73	Achieving low sub-0.6-nm EOT in gate-first n-MOSFET with TiLaO/CeO ₂ gate stack. Solid-State Electronics, 2013, 82, 111-114.	1.4	2
74	Gate-first n-MOSFET with a sub-0.6-nm EOT gate stack. Microelectronic Engineering, 2013, 109, 35-38.	2.4	8
75	High performance RF passive devices and noise-shielding MOSFET on IC-standard Si wafer for sub-THz applications. , 2013, , .		0
76	Evolution of the conductivity type in germania by varying the stoichiometry. Applied Physics Letters, 2013, 103, .	3.3	6
77	Current uniformity improvement in flexible resistive memory. , 2013, , .		0
78	(Invited) Ultra-Low Switching Power RRAM Using Hopping Conduction Mechanism. ECS Transactions, 2013, 50, 3-8.	0.5	3
79	Genome-wide discovery of gene isoforms expressed in primary smooth muscle cells. FASEB Journal, 2013, 27, 939.9.	0.5	0
80	A 2.4 GHz CMOS power amplifier using asymmetric MOSFETs. , 2012, , .		1
81	Improved current distribution in resistive memory on flexible substrate using nitrogen-rich TaN electrode. Applied Physics Letters, 2012, 101, .	3.3	11
82	Advanced metal-gate/high-κ CMOS with small EOT and better high field mobility. , 2012, , .		0
83	Bipolar conductivity in nanocrystallized TiO ₂ . Applied Physics Letters, 2012, 101, .	3.3	9
84	Ohmic contact on n-type Ge using Yb-germanide. Applied Physics Letters, 2012, 101, 223501.	3.3	13
85	Ge technology beyond Si CMOS. IOP Conference Series: Materials Science and Engineering, 2012, 41, 012002.	0.6	2
86	High-κ Gate Dielectrics for Ge CMOS and Related Memory Devices. , 2012, , .		0
87	Investigation of Schottky junction and MOS technology for III-V compound semiconductor MOSFET application. , 2012, , .		1
88	Design of a CMOS T/R Switch With High Power Capability: Using Asymmetric Transistors. IEEE Microwave and Wireless Components Letters, 2012, 22, 645-647.	3.2	8
89	Mechanism of GeO ₂ resistive switching based on the multi-phonon assisted tunneling between traps. Applied Physics Letters, 2012, 100, 243506.	3.3	63
90	A Bias-Variied Low-Power K-band VCO in 90 nm CMOS Technology. IEEE Microwave and Wireless Components Letters, 2012, 22, 321-323.	3.2	14

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91	High-Performance GaN MOSFET With High- κ $\text{LaAlO}_3/\text{SiO}_2$ Gate Dielectric. IEEE Electron Device Letters, 2012, 33, 35-37.	3.9	79
92	Transapical beating heart cardioscopy technique for off-pump visualization of heart valves. Journal of Thoracic and Cardiovascular Surgery, 2012, 144, 231-234.	0.8	15
93	Highly uniform low-power resistive memory using nitrogen-doped tantalum pentoxide. Solid-State Electronics, 2012, 73, 60-63.	1.4	14
94	High-Performance Charge-Trapping Flash Memory Device With an Ultrathin 2.5-nm Equivalent- Si_3N_4 -Thickness Trapping Layer. IEEE Transactions on Electron Devices, 2012, 59, 252-254.	3.0	5
95	A Dual-Resonant Mode 10/22-GHz VCO With a Novel Inductive Switching Approach. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 2165-2177.	4.6	32
96	High performance charge-trapping flash memory with highly-scaled trapping layer. , 2011, , .		1
97	Oxide-based RRAM: Unified microscopic principle for both unipolar and bipolar switching. , 2011, , .		58
98	Ultralow Switching Energy Ni/ GeO_x /HfON/TaN RRAM. IEEE Electron Device Letters, 2011, 32, 366-368.	3.9	37
99	Long-Endurance Nanocrystal TiO_2 Resistive Memory Using a TaON Buffer Layer. IEEE Electron Device Letters, 2011, 32, 1749-1751.	3.9	34
100	Arsenic-Implanted HfON Charge-Trapping Flash Memory With Large Memory Window and Good Retention. IEEE Electron Device Letters, 2011, 32, 381-383.	3.9	15
101	Bipolar conductivity in amorphous HfO_2 . Applied Physics Letters, 2011, 99, .	3.3	19
102	High-field mobility metal-gate/high- \hat{n} Ge n-MOSFETs with small equivalent-oxide-thickness. Solid-State Electronics, 2011, 55, 64-67.	1.4	6
103	Low-Power High-Performance Non-Volatile Memory on a Flexible Substrate with Excellent Endurance. Advanced Materials, 2011, 23, 902-905.	21.0	130
104	Bipolar switching characteristics of low-power GeO resistive memory. Solid-State Electronics, 2011, 62, 90-93.	1.4	5
105	Unipolar Ni/ GeO_x /PbZr $_{0.5}$ Ti $_{0.5}$ O $_3$ /TaN Resistive Switching Memory. Japanese Journal of Applied Physics, 2011, 50, 121801.	1.5	2
106	Higher Gate Capacitance Ge n-MOSFETs Using Laser Annealing. IEEE Electron Device Letters, 2011, 32, 449-451.	3.9	16
107	Stacked GeO/SrTiOx Resistive Memory with Ultralow Resistance Currents. Applied Physics Letters, 2011, 98, .	3.3	29
108	The Reliability Study and Device Modeling for p-HEMT Microwave Power Transistors. ECS Transactions, 2011, 41, 175-187.	0.5	0

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109	Size-Dependent Trapping Effect in Nano-Dot Non-Volatile Memory. ECS Transactions, 2011, 41, 121-132.	0.5	0
110	Unipolar Ni/GeO ₂ /PbZr _{0.5} Ti _{0.5} O ₃ /TaN Resistive Switching Memory. Japanese Journal of Applied Physics, 2011, 50, 121801.	1.5	2
111	High-Performance Gate-First Epitaxial Ge n-MOSFETs on Si With LaAlO_3 Gate Dielectrics. IEEE Transactions on Electron Devices, 2010, 57, 3525-3530.	3.0	4
112	Higher- κ titanium dioxide incorporating LaAlO ₃ as dielectrics for MIM capacitors. Solid-State Electronics, 2010, 54, 646-649.	1.4	2
113	A Study on Frequency-Dependent Voltage Nonlinearity of SrTiO ₃ rf Capacitor. Electrochemical and Solid-State Letters, 2010, 13, H436.	2.2	7
114	A Low Operating Voltage ZnO Thin Film Transistor Using a High- κ HfLaO Gate Dielectric. Electrochemical and Solid-State Letters, 2010, 13, H8.	2.2	13
115	Lanthanide-Oxides Mixed TiO ₂ Dielectrics for High- κ MIM Capacitors. Journal of the Electrochemical Society, 2010, 157, H821.	2.9	3
116	Highly scaled charge-trapping layer of ZrON nonvolatile memory device with good retention. Applied Physics Letters, 2010, 97, .	3.3	15
117	A Nonvolatile InGaZnO Charge-Trapping-Engineered Flash Memory With Good Retention Characteristics. IEEE Electron Device Letters, 2010, 31, 201-203.	3.9	40
118	Very high performance non-volatile memory on flexible plastic substrate. , 2010, , .		9
119	Design of Dual-Passband Microstrip Bandpass Filters With Multi-Spurious Suppression. IEEE Microwave and Wireless Components Letters, 2010, 20, 199-201.	3.2	36
120	Metal-gate/high- κ ; CMOS scaling from Si to Ge at small EOT. , 2010, , .		1
121	High- κ TiCeO MIM Capacitors with a Dual-Plasma Interface Treatment. Electrochemical and Solid-State Letters, 2010, 13, H112.	2.2	1
122	Improved Radio Frequency Power Characteristics of Complementary Metal-Oxide-Semiconductor-Compatible Asymmetric-Lightly-Doped-Drain Metal-Oxide-Semiconductor Transistor. Japanese Journal of Applied Physics, 2010, 49, 034201.	1.5	0
123	The Role of High- κ TiHfO Gate Dielectric in Sputtered ZnO Thin-Film Transistors. Japanese Journal of Applied Physics, 2010, 49, 04DA12.	1.5	3
124	Radio Frequency Power Performance Enhancement for Asymmetric Lightly Doped Drain Metal-Oxide-Semiconductor Field-Effect Transistors on SiC Substrate. Japanese Journal of Applied Physics, 2010, 49, 014104.	1.5	0
125	High performance ultra-low energy RRAM with good retention and endurance. , 2010, , .		61
126	Improved Capacitance Density and Reliability of High- κ $\text{Ni}/\text{ZrO}_2/\text{TiN}$ MIM Capacitors Using Laser-Annealing Technique. IEEE Electron Device Letters, 2010, 31, 749-751.	3.9	41

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127	Characteristics of Cerium Oxide for Metal-Insulator-Metal Capacitors. Electrochemical and Solid-State Letters, 2010, 13, H16.	2.2	14
128	A Low-Power K-Band CMOS VCO With Four-Coil Transformer Feedback. IEEE Microwave and Wireless Components Letters, 2010, 20, 459-461.	3.2	34
129	Highly-scaled 3.6-nm ENT trapping layer MONOS device with good retention and endurance. , 2010, , .		19
130	Gate-First $\text{TaN/La}_2\text{O}_3/\text{SiO}_2/\text{Ge}$ n-MOSFETs Using Laser Annealing. IEEE Electron Device Letters, 2010, , .	3.9	3
131	High Performance of Ge nMOSFETs Using SiO_2 Interfacial Layer and TiLaO Gate Dielectric. IEEE Electron Device Letters, 2010, 31, 80-82.	3.9	14
132	Novel Ultra-low power RRAM with good endurance and retention. , 2010, , .		56
133	Higher $\text{TaN}/\text{SiO}_2/\text{Ge}$ n-MOSFETs with <1 nm EOT using laser annealing. , 2010, , .		4
134	Low-Voltage-Driven Flexible InGaZnO Thin-Film Transistor With Small Subthreshold Swing. IEEE Electron Device Letters, 2010, 31, 680-682.	3.9	57
135	Ultralow-Power Ni/GeO ₂ /STO/TaN Resistive Switching Memory. IEEE Electron Device Letters, 2010, 31, 1020-1022.	3.9	18
136	High-Performance InGaZnO Thin-Film Transistors Using HfLaO Gate Dielectric. IEEE Electron Device Letters, 2009, 30, 1317-1319.	3.9	86
137	Low-Threshold-Voltage MoN/HfAlO/SiON p-MOSFETs With 0.85-nm EOT. IEEE Electron Device Letters, 2009, 30, 861-863.	3.9	18
138	Improved retention and cycling characteristics of MONOS memory using Charge-Trapping-Engineering. , 2009, , .		3
139	Design of dual-passband microstrip bandpass filters with suppression of higher order spurious response. , 2009, , .		3
140	Effect of Ta ₂ O ₅ Doping on Electrical Characteristics of SrTiO ₃ Metal-Insulator-Metal Capacitors. Japanese Journal of Applied Physics, 2009, 48, 081401.	1.5	2
141	Improved Device Characteristics in Charge-Trapping-Engineered Flash Memory Using High-k Dielectrics. ECS Transactions, 2009, 25, 447-455.	0.5	5
142	Improved Lower Electrode Oxidation of High-k TiCeO Metal-Insulator-Metal Capacitors by Using Dual Plasma Treatment. ECS Transactions, 2009, 16, 323-333.	0.5	0
143	Flat band voltage control on low V_t metal-gate/high- ϵ_r CMOSFETs with small EOT (Invited Paper). Microelectronic Engineering, 2009, 86, 1728-1732.	2.4	4
144	High-Density and Low-Leakage-Current MIM Capacitor Using Stacked $\text{TiO}_2/\text{ZrO}_2$ Insulators. IEEE Electron Device Letters, 2009, 30, 715-717.	3.9	34

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145	Low-Threshold-Voltage TaN/LaTiO n-MOSFETs With Small EOT. IEEE Electron Device Letters, 2009, 30, 999-1001.	3.9	12
146	Improved Stress Reliability of Analog Metal-Insulator-Metal Capacitors Using $\text{TiO}_2/\text{ZrO}_2$ Dielectrics. IEEE Electron Device Letters, 2009, 30, 1287-1289.	3.9	10
147	Low-Threshold-Voltage TaN/Ir/LaTiO p-MOSFETs Incorporating Low-Temperature-Formed Shallow Junctions. IEEE Electron Device Letters, 2009, 30, 681-683.	3.9	4
148	Small-Subthreshold-Swing and Low-Voltage Flexible Organic Thin-Film Transistors Which Use HfLaO as the Gate Dielectric. IEEE Electron Device Letters, 2009, 30, 133-135.	3.9	59
149	Low- V_{t} TaN/HfLaO n-MOSFETs Using Low-Temperature Formed Source-Drain Junctions. IEEE Electron Device Letters, 2009, 30, 75-77.	3.9	6
150	Interfacial layer dependence on device property of high- κ TiLaO Ge/Si N-type metal-oxide-semiconductor capacitors at small equivalent-oxide thickness. Applied Physics Letters, 2009, 95, .	3.3	21
151	National Project on 45 to 32 nm Metal Oxide Semiconductor Field Effect Transistors for Next Century IC Fabrications. E-Journal of Surface Science and Nanotechnology, 2009, 7, 507-512.	0.4	1
152	High-Work-Function Ir/HfLaO m -MOSFETs Using Low-Temperature-Processed Shallow Junction. IEEE Transactions on Electron Devices, 2008, 55, 838-843.	3.0	3
153	Comparison of MONOS Memory Device Integrity When Using $\text{Hf}_{1-x}\text{N}_x\text{O}_y$ Trapping Layers With Different N Compositions. IEEE Transactions on Electron Devices, 2008, 55, 1417-1423.	3.0	52
154	Improving the Retention and Endurance Characteristics of Charge-Trapping Memory by Using Double Quantum Barriers. IEEE Transactions on Electron Devices, 2008, 55, 1708-1713.	3.0	6
155	Improvement of the Performance of TiHfO MIM Capacitors by Using a Dual Plasma Treatment of the Lower Electrode. IEEE Electron Device Letters, 2008, 29, 1105-1107.	3.9	19
156	Improved RF Power Performance in a 0.18- μm MOSFET Which Uses an Asymmetric Drain Design. IEEE Electron Device Letters, 2008, 29, 1402-1404.	3.9	3
157	A flexible organic pentacene nonvolatile memory based on high- κ dielectric layers. Applied Physics Letters, 2008, 93, .	3.3	44
158	High Density and Low Leakage Current in TiO_2 MIM Capacitors Processed at 300 $^{\circ}\text{C}$. IEEE Electron Device Letters, 2008, 29, 845-847.	3.9	62
159	Low Subthreshold Swing HfLaO/Pentacene Organic Thin-Film Transistors. IEEE Electron Device Letters, 2008, 29, 215-217.	3.9	46
160	New Test Structure to Monitor Contact-to-Poly Leakage in Sub-90 nm CMOS Technologies. IEEE Transactions on Semiconductor Manufacturing, 2008, 21, 244-247.	1.7	3
161	Gate-First Low V_{t} Al/TaN/Ir/HfLaO p-MOSFET Using Simple Laser Annealing. , 2008, , .		0
162	High-Performance MIM Capacitors Using a High- κ TiZrO Dielectric. Journal of the Electrochemical Society, 2008, 155, G295.	2.9	8

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163	Improved high temperature retention and endurance in HfON trapping memory with double quantum barriers. , 2008, , .		0
164	Widely Tunable Work Function TaN/Ru Stacking Layer on HfLaO Gate Dielectric. IEEE Electron Device Letters, 2008, 29, 50-53.	3.9	9
165	Crucial integration of high work-function metal gate and high-k blocking oxide on charge-trapping type flash memory device. Applied Physics Letters, 2008, 93, .	3.3	12
166	National project on 45 to 32 nm metal oxide semiconductor field effect transistors for next century IC fabrications. , 2008, , .		1
167	Good 150°C retention and fast erase characteristics in charge-trap-engineered memory having a scaled Si–N–Si layer. , 2008, , .		8
168	A CMOS-compatible, high RF power, Asymmetric-LDD MOSFET with excellent linearity. , 2008, , .		10
169	Improved High Temperature Retention for Charge-Trapping Memory by Using Double Quantum Barriers. IEEE Electron Device Letters, 2008, 29, 386-388.	3.9	12
170	High Performance Ir/TiPrO/TaN MIM Capacitors for Analog ICs Application. ECS Transactions, 2008, 16, 341-352.	0.5	1
171	Improvement of the Performance of Strained 0.13 μm MOSFETs Mounted on Flexible Plastic Substrates. , 2007, , .		1
172	Very High Density ($44 \times 10^4 \text{ m}^{-2}$) SrTiO ₃ MIM Capacitors for RF Applications. Journal of the Electrochemical Society, 2007, 154, H214.	2.9	10
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174	Improved Stress Reliability of Analog TiHfO Metal-Insulator-Metal Capacitors Using High-Work-Function Electrode. Japanese Journal of Applied Physics, 2007, 46, 7300.	1.5	15
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344	Very low defects and high performance Ge-on-insulator p-MOSFETs with Al/sub 2/O/sub 3/ gate dielectrics. , 0, , .		20
345	Investigation of performance limits of germanium double-gated MOSFETs. , 0, , .		27
346	Microwave coplanar filters on Si substrates. , 0, , .		4
347	Electrically stimulated cell membrane breakdown in human placenta TL and lung cancer cell A549 in 3D trap arrays on Si substrate. , 0, , .		1
348	Germanium MOS: an evaluation from carrier quantization and tunneling current. , 0, , .		6
349	Light emission from Al/sub 2/O/sub 3//Si/sub 1-x/Ge/sub x//Si MOS tunnel diodes. , 0, , .		0
350	The minimum noise figure and mechanism as scaling RF MOSFETs from 0.18 to 0.13 $\hat{1}$ / ₄ m technology nodes. , 0, , .		15
351	Low temperature MOSFET technology with Schottky barrier source/drain, high-K gate dielectrics and metal gate electrode. , 0, , .		0
352	High density RF MIM capacitors using high- $\hat{1}$ ^p AlTaO/sub x/ dielectrics. , 0, , .		7
353	1.3 $\hat{1}$ / ₄ m light emission from Al/sub 2/O/sub 3//Si/sub 1-x/Ge/sub x//Si MOS tunnel diodes. , 0, , .		0
354	Low RF loss and noise of transmission lines on Si substrates using an improved ion implantation process. , 0, , .		14
355	RF noise scaling trend of MOSFETs from 0.5 $\hat{1}$ / ₄ m to 0.13 $\hat{1}$ / ₄ m technology nodes. , 0, , .		13
356	A novel surface passivation process for HfO/sub 2/ Ge MOSFETs. , 0, , .		0
357	High performance metal-gate/high-k MOSFETs and GaAs compatible RF passive devices on Ge-on-insulator technology. , 0, , .		1
358	Low workfunction fully silicided gate on SiO/sub 2//Si and LaAlO/sub 3//GOI n-MOSFETs. , 0, , .		2
359	Impact of surface roughness on silicon and germanium ultra-thin-body MOSFETs. , 0, , .		15
360	Narrow-band band-pass filters on silicon substrates at 30 GHz. , 0, , .		18

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362	Modeling finger number dependence on RF noise to 10 GHz in 0.13 $\hat{1}$ / ₄ m node MOSFETs with 80nm gate length. , 0, , .		16
363	3D GOI CMOSFETs with novel IrO/sub 2/2(Hf) dual gates and high-K dielectric on 1P6M-0.18 $\hat{1}$ / ₄ m-CMOS. , 0, , .		19
364	Schottky s/d MOSFETs with high-K gate dielectrics and imetal gate electrodes. , 0, , .		0
365	A comparison study of high-density MIM capacitors with ALD HfO/sub 2/-Al/sub 2/O/sub 3/ laminated, sandwiched and stacked dielectrics. , 0, , .		0
366	Novel SiO/sub 2/AlN/HfAlO/IrO/sub 2/ memory with fast erase, large $\hat{1}$ "V/sub TH/ and good retention. , 0, , .		23
367	Low Noise and High Gain RF MOSFETs on Plastic Substrates. , 0, , .		3
368	Very High Density RF MIM Capacitor Compatible with VLSI. , 0, , .		7
369	Strain-induced very low noise RF MOSFETs on flexible plastic substrate. , 0, , .		19
370	Physics and modeling of Ge-on-insulator MOSFETs. , 0, , .		5
371	Very high K and high density TiTaO MIM capacitors for analog and RF applications. , 0, , .		27
372	Modeling RF MOSFETs after electrical stress using low-noise microstrip line layout. , 0, , .		12
373	Advanced MOSFETs using HfTaON/SiO/sub 2/ gate dielectric and TaN metal gate with excellent performances for low standby power application. , 0, , .		3
374	Dual Metal Gates with Band-Edge Work Functions on Novel HfLaO High-K Gate Dielectric. , 0, , .		19
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